



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low Gate Charge
- Low R_{DS(ON)}:
 - 24mΩ @V_{GS} = 4.5V
 - $28m\Omega$ @V_{GS} = 2.5V
 - $34m\Omega$ @V_{GS} = 1.8V
- Low Input/Output Leakage
- ESD Protected up to 2kV HBM
- Lead Free By Design/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 4)

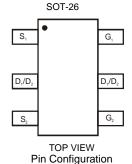
Mechanical Data

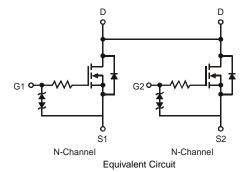
- Case: SOT-26
- Case Material Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.0008 grams (approximate)





TOP VIEW





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	20	V
Gate-Source Voltage		V_{GSS}	±12	V
Drain Current (Note 1) Continuous	$T_A = 25$ °C $T_A = 70$ °C	I _D	6.5 5.2	А
Pulsed Drain Current (Note 2)		I _{DM}	30	A

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P _D	0.85	W
Thermal Resistance, Junction to Ambient (Note 1) t ≤10s	$R_{ heta JA}$	147	°C /W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width $t \le 10s$.
- 2. Repetitive Rating, pulse width limited by junction temperature.
- 3. No purposefully added lead.
- 4. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

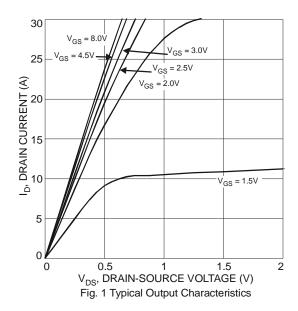


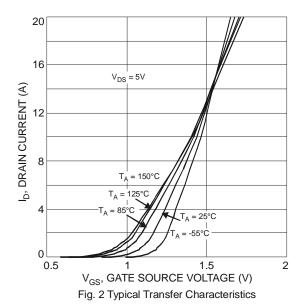
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
STATIC CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	20		_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}			1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Body Leakage Current	Igss			±10	μΑ	$V_{DS} = 0V, V_{GS} = \pm 10V$	
Gate-Source Breakdown Voltage	BV _{SGS}	±12	ī	-	V	$V_{DS} = 0V$, $I_{G} = \pm 250 \mu A$	
Gate Threshold Voltage	V _{GS(th)}	0.5	_	0.9	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance (Note 5)	R _{DS (ON)}	_	17 20 26	24 28 34	mΩ	$V_{GS} = 4.5V$, $I_D = 6.5A$ $V_{GS} = 2.5V$, $I_D = 5.5A$ $V_{GS} = 1.8V$, $I_D = 3.5A$	
Forward Transfer Admittance	Y _{FS}	_	8	_	S	$V_{DS} = 10V, I_D = 5A$	
Diode Forward Voltage (Note 5)	V _{SD}	_	0.7	1.0	V	I _S = 2.25A, V _{GS} = 0V	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C _{iss}	_	143	_	pF	10// // 0//	
Output Capacitance	Coss	_	74	—	pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		29	_	pF	1 = 1:001112	
Gate Resisitance	R_{G}		202	_	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1MHz$	
SWITCHING CHARACTERISTICS							
Total Gate Charge	Q_{g}		8.8	_	nC		
Gate-Source Charge	Q_{gs}		1.4	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6.5A$	
Gate-Drain Charge	Q_{gd}		3.0	_	nC]	
Turn-On Delay Time	t _{D(on)}		53	_	ns		
Turn-On Rise Time	t _r		78	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(off)}		562	_	ns	$R_L = 10\Omega$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _f		234	_	ns		

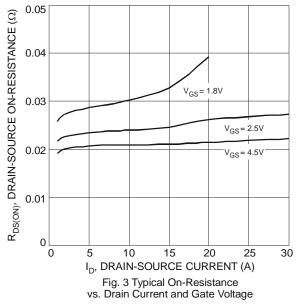
Notes:

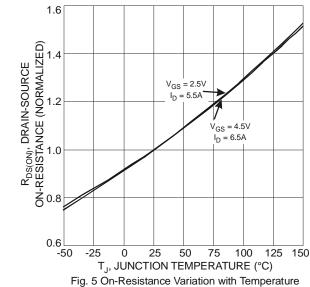
- 5. Test pulse width t = 300ms.
- 6. Guaranteed by design. Not subject to production testing.











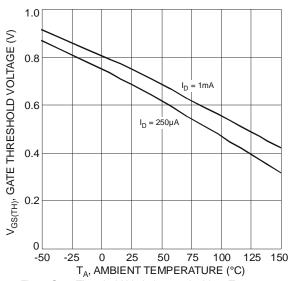


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

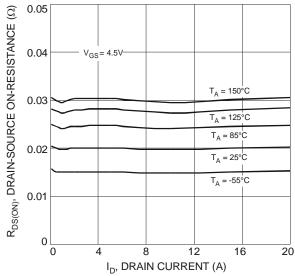


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

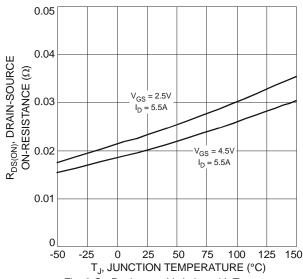
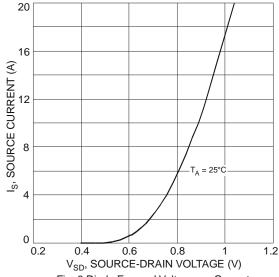
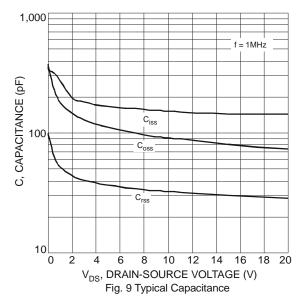


Fig. 6 On-Resistance Variation with Temperature







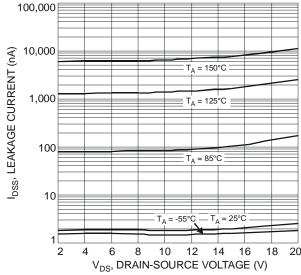


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

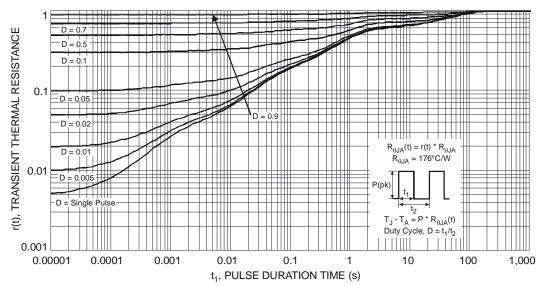


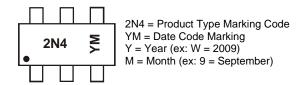
Fig. 11 Transient Thermal Response

Ordering Information (Note 7)

Part Number	Case	Packaging
DMG6968UDM-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

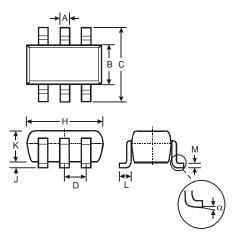


Date Code Key

i cai	2000		2003	2010		2011	2012	•	2013	2014	•	2013
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

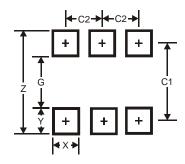


Package Outline Dimensions



	SOT-26						
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D	_	_	0.95				
Н	2.90	3.10	3.00				
J	0.013	0.10	0.05				
K	1.00	1.30	1.10				
L	0.35	0.55	0.40				
М	0.10	0.20	0.15				
α	0°	8°					
All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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